EH2645ETTTS-10.000M



- Nominal Frequency

10.000MHz

L Pin 1 Connection

Duty Cycle 50 ±5(%)

Tri-State (High Impedance)

Series -RoHS Compliant (Pb-free) 3.3V 4 Pad 5mm x 7mm Ceramic SMD LVCMOS High Frequency Oscillator

Frequency Tolerance/Stability ±50ppm Maximum

Operating Temperature Range --40°C to +85°C

ELECTRICAL SPECIFICATIONS

Nominal Frequency	10.000MHz
Frequency Tolerance/Stability	±50ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Output Load Change, First Year Aging at 25°C, Shock, and Vibration)
Aging at 25°C	±5ppm/year Maximum
Operating Temperature Range	-40°C to +85°C
Supply Voltage	3.3Vdc ±0.3Vdc
Input Current	35mA Maximum (No Load)
Output Voltage Logic High (Voh)	2.7Vdc Minimum (IOH= -8mA)
Output Voltage Logic Low (Vol)	0.5Vdc Maximum (IOH= +8mA)
Rise/Fall Time	6nSec Maximum (Measured at 20% to 80% of waveform)
Duty Cycle	50 ±5(%) (Measured at 50% of waveform)
Load Drive Capability	30pF Maximum
Output Logic Type	CMOS
Pin 1 Connection	Tri-State (High Impedance)
Tri-State Input Voltage (Vih and Vil)	70% of Vdd Minimum to enable output, 20% of Vdd Maximum to disable output, No Connect to enable output.
Absolute Clock Jitter	±250pSec Maximum, ±100pSec Typical
One Sigma Clock Period Jitter	±50pSec Maximum, ±40pSec Typical
Start Up Time	10mSec Maximum
Storage Temperature Range	-55°C to +125°C

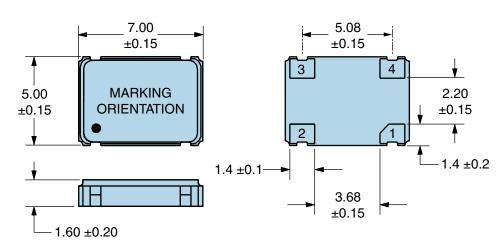
EH26 45 ET T TS -10.000M

ENVIRONMENTAL & MECHANICAL SPECIFICATIONS

ESD Susceptibility	MIL-STD-883, Method 3015, Class 1, HBM: 1500V	
Fine Leak Test	MIL-STD-883, Method 1014, Condition A	
Flammability	UL94-V0	
Gross Leak Test	MIL-STD-883, Method 1014, Condition C	
Mechanical Shock	MIL-STD-883, Method 2002, Condition B	
Moisture Resistance	MIL-STD-883, Method 1004	
Moisture Sensitivity	J-STD-020, MSL 1	
Resistance to Soldering Heat	MIL-STD-202, Method 210, Condition K	
Resistance to Solvents	MIL-STD-202, Method 215	
Solderability	MIL-STD-883, Method 2003	
Temperature Cycling	MIL-STD-883, Method 1010, Condition B	
Vibration	MIL-STD-883, Method 2007, Condition A	

EH2645ETTTS-10.000M

MECHANICAL DIMENSIONS (all dimensions in millimeters)



PIN	CONNECTION	
1	Tri-State (High Impedance)	
2	Ground	
3	Output	
4	Supply Voltage	
LINE MARKING		
	MARRING	
1	ECLIPTEK	
2	10.000M	
3	XXXXXX XXXXX=Ecliptek Manufacturing Identifier	

Suggested Solder Pad Layout

All Dimensions in Millimeters



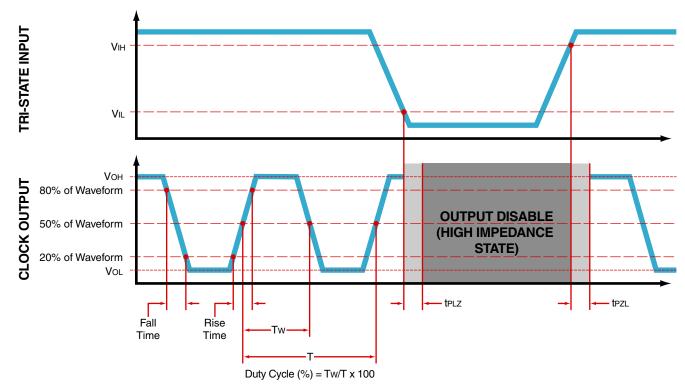
All Tolerances are ±0.1



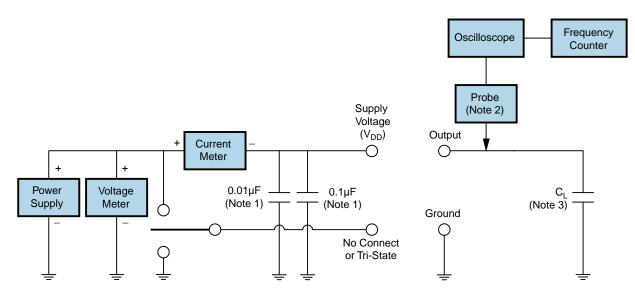
EH2645ETTTS-10.000M



OUTPUT WAVEFORM & TIMING DIAGRAM



Test Circuit for CMOS Output



Note 1: An external 0.1μ F low frequency tantalum bypass capacitor in parallel with a 0.01μ F high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value \dot{C}_L includes sum of all probe and fixture capacitance.



Recommended Solder Reflow Methods

EH2645ETTTS-10.000M



High Temperature Infrared/Convection

T_s MAX to T_L (Ramp-up Rate)	3°C/second Maximum
Preheat	
- Temperature Minimum (T _s MIN)	150°C
 Temperature Typical (T_s TYP) 	175°C
 Temperature Maximum (T_s MAX) 	200°C
- Time (t _s MIN)	60 - 180 Seconds
Ramp-up Rate (T _L to T _P)	3°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	217°C
- Time (t∟)	60 - 150 Seconds
Peak Temperature (T _P)	260°C Maximum for 10 Seconds Maximum
Target Peak Temperature (T _P Target)	250°C +0/-5°C
Time within 5°C of actual peak (t _p)	20 - 40 seconds
Ramp-down Rate	6°C/second Maximum
Time 25°C to Peak Temperature (t)	8 minutes Maximum
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.



Recommended Solder Reflow Methods

EH2645ETTTS-10.000M



Low Temperature Infrared/Convection 240°C

T _s MAX to T _L (Ramp-up Rate)	5°C/second Maximum
Preheat	
- Temperature Minimum (T _s MIN)	N/A
 Temperature Typical (T_s TYP) 	150°C
 Temperature Maximum (T_s MAX) 	N/A
- Time (t _s MIN)	60 - 120 Seconds
Ramp-up Rate (T⊾ to T _P)	5°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	150°C
- Time (t∟)	200 Seconds Maximum
Peak Temperature (T _P)	240°C Maximum
Target Peak Temperature (T _P Target)	240°C Maximum 1 Time / 230°C Maximum 2 Times
Time within 5°C of actual peak (t _P)	10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time
Ramp-down Rate	5°C/second Maximum
Time 25°C to Peak Temperature (t)	N/A
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.

Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

High Temperature Manual Soldering

260°C Maximum for 5 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)